RELIABILITY REPORT

FOR

MAX3660ETE+

PLASTIC ENCAPSULATED DEVICES

March 18, 2009

MAXIM INTEGRATED PRODUCTS

120 SAN GABRIEL DR.

SUNNYVALE, CA 94086

Approved by
Ken Wendel
Quality Assurance
Director, Reliability Engineering

Conclusion

The MAX3660ETE+ successfully meets the quality and reliability standards required of all Maxim products. In addition, Maxim"s continuous reliability monitoring program ensures that all outgoing product will continue to meet Maxim"s quality and reliability standards.

Table of Contents

I. Device Description

A. General

The MAX3660 high-linearity analog RF transimpedance amplifier (TIA) is intended for passive optical network (PON) video receiver applications. With 66dB maximum variable gain and integrated uptilt, the MAX3660 provides 23dBmV/channel ±1dB at 870MHz (19dBmV/channel at 47MHz) for optical inputs between +2dBm to -8dBm (at 4.2% OMI) using simple feed-forward automatic gain control (AGC). It can also be configured with feedback AGC for even greater dynamic range. CNR is better than 48dB from 47MHz to 870MHz (1.0A/W photodiode and -165dB/Hz RIN) at -8dBm with 4.2% OMI, or -6dBm with 3.3% OMI. CSO and CTB are better than -61dBc and -65dBc, respectively. The device supports extended frequency operation to > 1000MHz. The very low true-TIA input impedance accommodates a variety of photodiodes, eliminating the need for an input matching network and improving yield.

II. Manufacturing Information

A. Description/Function:	Analog CATV Transimpedance Amplifier
B. Process:	MFN SiGe HBT CMOS (G4)
C. Number of Device Transistors:	
D. Fabrication Location:	Oregon
E. Assembly Location:	ASAT China, UTL Thailand
F. Date of Initial Production:	July 26, 2008

III. Packaging Information

A. Package Type:	16-pin TQFN 4x4
B. Lead Frame:	Copper
C. Lead Finish:	100% matte Tin
D. Die Attach:	Conductive Epoxy
E. Bondwire:	Gold (1 mil dia.)
F. Mold Material:	Epoxy with silica filler
G. Assembly Diagram:	#05-9000-2751
H. Flammability Rating:	Class UL94-V0
I. Classification of Moisture Sensitivity per JEDEC standard J-STD-020-C	Level 1
J. Single Layer Theta Ja:	59.3°C/W
K. Single Layer Theta Jc:	5.7°C/W
L. Multi Layer Theta Ja:	40°C/W
M. Multi Layer Theta Jc:	5.7°C/W

IV. Die Information

A. Dimensions:	88 X 88 mils
B. Passivation:	Si_3N_4
C. Interconnect:	Au
D. Backside Metallization:	None
E. Minimum Metal Width:	1.2 microns (as drawn) Metal 1, 2 & 3 5.6 microns (as drawn) Metal 4
F. Minimum Metal Spacing:	1.6 microns (as drawn) Metal 1, 2 & 3, 4.2 microns (as drawn) Metal 4
G. Bondpad Dimensions:	5 mil. Sq.
H. Isolation Dielectric:	SiO_2
I. Die Separation Method:	Wafer Saw

V. Quality Assurance Information

A. Quality Assurance Contacts:	Ken Wendel (Director, Reliability Engineering) Bryan Preeshl (Managing Director of QA)
B. Outgoing Inspection Level:	0.1% for all electrical parameters guaranteed by the Datasheet. 0.1% For all Visual Defects.
C. Observed Outgoing Defect Rate:	< 50 ppm
D. Sampling Plan:	Mil-Std-105D

VI. Reliability Evaluation

A. Accelerated Life Test

The results of the 135°C biased (static) life test are shown in Table 1. Using these results, the Failure Rate (λ) is calculated as follows:

$$\lambda = \frac{1}{MTTF} = \frac{1.83}{192 \times 4340 \times 48 \times 2}$$ (Chi square value for MTTF upper limit)

(where 4340 = Temperature Acceleration factor assuming an activation energy of 0.8eV)

$\lambda = 22.4 \times 10^{-9}$

λ = 22.4 F.I.T. (60% confidence level @ 25°C)

The following failure rate represents data collected from Maxim's reliability monitor program. Maxim performs quarterly 1000 hour life test monitors on its processes. This data is published in the Product Reliability Report found at http://www.maxim-ic.com/. Current monitor data for the G4 Process results in a FIT Rate of 0.2 @ 25C and 3.6 @ 55C (0.8 eV, 60% UCL)

B. Moisture Resistance Tests

The industry standard 85°C/85%RH or HAST testing is monitored per device process once a quarter.

C. E.S.D. and Latch-Up Testing

The HD97 die type has been found to have all non high frequency pins able to withstand a HBM transient pulse of +/-2500 V per JEDEC JESD22-A114. Latch-Up testing has shown that this device withstands a current of +/-250 mA, 1.5x VCCMax Overvoltage per JESD78.

Table 1
Reliability Evaluation Test Results

MAX3660ETE+

TEST ITEM	TEST CONDITION	FAILURE IDENTIFICATION	SAMPLE SIZE	NUMBER OF FAILURES
Static Life Test (Note 1)				
	Ta = 135°C Biased Time = 192 hrs.	DC Parameters & functionality	48	0
Moisture Testing (Note 2)				
85/85	Ta = 85°C RH = 85% Biased Time = 1000hrs.	DC Parameters & functionality	77	0
Mechanical Stress (Note 2)				
Temperature Cycle	-65°C/150°C 1000 Cycles Method 1010	DC Parameters & functionality	77	0

Note 1: Life Test Data may represent plastic DIP qualification lots.
Note 2: Generic Package/Process data